5 é / Descriptions

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Schottky Barrier Diode in a TO-220F Plastic Package.

¤ ª / Features

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Low poer losses, High efficiency operation.

Ð ÷ / Applications

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For use in high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

Ã W] Ô · / Equivalent Circuit

• Û - æ / Pinning

PIN1 y Anode PIN 2 y Cathode PIN 3 y Anode

, M V / Marking

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See Marking Instructions.

Ô4ì × ? d / Electrical Characteristics(Ta=25 ;)

@ ƒ Parameter	… Z Symbol	ƒ › Rating MBRFXXCT						% y Unit
		2040	2045	2060	20100	20150	20200	
PeakRepetitive Reverse Voltage	V_{RM}	40	45	60	100	150	200	V
RMS Reverse Voltage	V_{RMS}	28	32	42	70	105	140	V
DC Blocking Voltage	V_{DC}	40	45	60	100	150	200	V
Average Rectified Forward Current	$I_{F(AV)}$	10X2						A
Forward Voltage at 10A	V_F	0.70		0.75	0.85	0.90	0.92	V
Instantaneous Ta=25 ƒC	I_R	0.1			0.05			mA
Reverse Current Ta=125 ƒC		20			20			
Typical Junction Capacitance (1)	C_J	600		400				pF
Non Repetitive Peak Surge Current	I_{FSM}	150						A
Thermal Resistance Junction to Case (2)	R_{JA}	45						ƒC/W
Junction and Storage Temperature Range	T_j T_{stg}	-55~150				-55~175		ƒC

Notes Ö

(1) Measured at 1 MHz and applied reverse voltage of 4 V D.C

(2) P.C.B. mounted with 10cmX10cmX1mm copper pad areas.

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